NK-121 (43

DEPARTMENT OF ELECTRONICS AND ELECTRICAL COMMUNICATION ENGINEERING INDIAN INSTITUTE OF TECHNOLOGY KHARAGPUR

Date: Seme Instruc	3161-2019, Sub. No.: EC21101, Sub. Name: Basic	60, No. of Students: 698 (Non-ECE branches); Mid Spring : Electronics
	All waveform sketches / diagrams must brief and to the point.	be neatly drawn and clearly labeled. Answers must be
		h unit) should be <u>underlined</u> or enclosed within box
•	For every Question No., start your answer Avoid writing answers of the various parameters.	er from a new page. arts of a single question at different locations in your
	For any value related to any device par	rameter or circuit parameter, which you may find not value for such parameter. V_{γ} stands for cut-in voltage as 0.7 V.
1. M	ultiple choice questions (only one corre	ect answer) (10×1=10 marks)
I.	(a) temperature	on (b) doping concentration
	(c) intrinsic concentration	(d) all of these
11.	Breakdown mechanism in a normal diode u (a) Zener breakdown (c) both (a) & (b)	nder reverse bias is (b) Avalanche breakdown (d) none of the above
m.	The current in a forward biased pn junction (a) the diffusion current (c) both diffusion and drift current	mainly consists of (b) the drift current (d) none of the above
IV.	With increase in temperature, the resistance (a) increases (c) remains constant	e of a semiconductor (b) decreases (d) varies non-monotonically
٧.	A capacitor is placed across a half/full-wave (a) short high frequency component (c) provide an almost constant output	e rectifier to (b) block the dc component (d) none of the above
VI.	A pn junction diode with a 100 Ω resistor is forward biased so that a current of 100 mA flows. If the voltage across this combination is instantaneously reversed to 10 V time t=0, the reverse current that flows through the diode at t=0 ⁺ is approximately given by, (a) 0 mA (b) 100 mA (c) 200 mA	
VII.	A pn junction has a donor atom concentration if the intrinsic carrier concentration is 10 ¹⁰ , (in volts) of the junction will be approximate (a) 0.66 (c) 0.29	on of 10 ¹⁵ /cm ³ and acceptor atom concentration of 10 ¹⁶ /cm ³ /cm ³ , then at room temperature (300K) the built in potentially. (b) 1.26 (d) 0.7
VIII.	A high-pass filter for a square input pulse w (a) Integrator	

(c) Both (a) & (b)

(d) None

A clamper circuit consists of an ideal diode, capacitor and a load resistor. When an input square wave signal (with peak value of a resistor) and a load resistor. When an input square wave IX. signal (with peak voltage of V_m) is applied to the circuit and the output is measured across the load/diode such that the V_m load/diode such that the diode conducts in the negative half cycle, then the output waveform will have the maximum amplitude of the maximum amplitude of

(a) V_m

(b) 2V_m

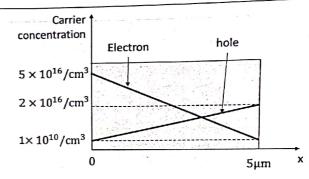
(c) -2V_m

- $(d) V_m$
- When a 50 Hz sinusoid signal with a peak voltage of 10 V is applied to a full-wave rectifier consist of an ideal diode and local voltage of 0.25 X. ideal diode and load resistance of 10 k Ω , the capacitance required to achieve the ripple voltage of 0.25 V will be V will be
 - (a) 40 μF

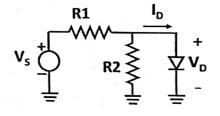
(b) 4 μF

(c) 80 µF

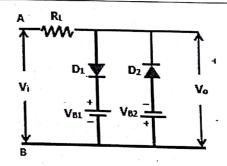
- (d) $8 \mu F$
- 2(a). Carrier concentration in a silicon substrate, as shown in figure, varies linearly where electron injection is from left and the hole injection is from right. Determine the current density and total current flowing through the device if the cross sectional area is equal to 1 µm². Also indicate the direction of the current flow. Silicon parameters: $\mu_n = 1400\,\text{cm}^2/\text{V.s.}$ $\mu_p =$ $470 \text{ cm}^2/\text{V.s.}$, $D_n = 34 \text{ cm}^2/\text{s.}$, $D_p = 12 \text{ cm}^2/\text{s.}$, electron charge = 1.602×10^{-19} C. [4 marks]



2(b). In the circuit as shown in right, the supply voltage is kept between 5V and 10V (10V≥V_s≥ 5V) in order to keep the diode 'on'. The minimum diode current (ID) is to be 2mA and the power dissipation in the diode should not cross 10mW. Using the piecewise linear model with $V_{\gamma}=0.7 V \, \text{and} \, r_f=10 \Omega,$ determine the appropriate values of R₁ and R₂. [6 marks]



3 (a). Consider the circuit shown in the right. Assume a sinusoidal voltage is applied to the input with amplitude $V_{i,max} > |V_{B1}|$, $|V_{B2}|$. (i) Draw the variation of the output voltage with time as the input varies sinusoidally. Put appropriate labels wherever required.

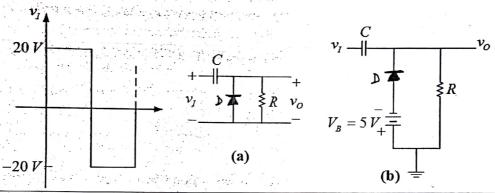


- 3(b) Draw the input-output characteristics when the input varies from $-2(V_{B2}+V_{B1})$ to $2(V_{B2}+V_{B1})$. Put appropriate labels wherever required [3 marks]
- **4.** A Zener diode regulator has a specified rating of $V_Z=10V$ at $I_Z^{min}=25mA$. The incremental Zener resistance is given to be $r_z = 5\Omega$.
- (a) Write down the linearized equation for the voltage across the Zener diode as a function of current for $V_Z >$ 10V. [2 marks]
- (b) If the maximum power rating of the Zener diode is 1W, from the equation derived in part (a), determine the maximum current that can flow through the Zener diode without damaging it.

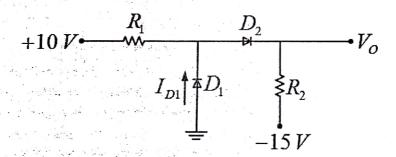
[4 marks]

(c) Determine the voltage at the maximum current that the Zener diode can withstand. [2 marks]

- Explain the mechanism to convert AC into desired DC with the help of different blocks. Sketch the waveform at every stage of the block. [4 marks]
- **5(b).** What type of rectifier circuit one should use and why? Explain the rectification mechanism and obtain the average dc output and ripple factor. [8 marks]
- **5(c).** Depending on your answer in (b), estimate the PIV of a diode used in that particular rectifier circuit. [2 marks]
- **6.** Sketch the steady-state output voltage v_o versus time for each circuit in (a) and (b) with the input voltage shown in the figure below. Assume $V_{\gamma} = 0.7V$ and the RC time constant to be large with respect to half-time period. [3+3 marks]



7. For the circuit shown in the figure below, let $V_{\gamma}=0.7V$ for each diode. Calculate I_{D1} and V_{O} for (a) $R_{1}=10~k\Omega$, $R_{2}=5~k\Omega$ and for (b) $R_{1}=5~k\Omega$, $R_{2}=10~k\Omega$. [3+3 marks]



End of Question Paper